AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

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Listing of Claims

Claim 1 (Currently Amended): A semiconductor light-emitting element mounting member comprising:

a substrate; and

a metal film formed on a surface of said substrate, formed from Ag, Al, or an alloy containing said metals, and functioning as an electrode layer for mounting at least one of a semiconductor light-emitting element and/or a reflective layer for reflecting light from a semiconductor light-emitting element;

wherein: the thickness of the metal film is 0.5 - $3 \mu m$ and crystal grains of said metal or alloy forming said metal film have a particle diameter along a surface plane of said metal film is no more than $0.5 \mu m$; and said surface of said metal film has a center-line average roughness Ra of no more than $0.1 \mu m$.

Claim 2 (Original): A semiconductor light-emitting element mounting member according to claim 1 wherein an adhesion layer and a barrier layer are formed, in sequence, on said substrate, with said metal film being formed on said barrier layer.

Claim 3 (Currently amended): A semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed as an alloy of <u>at least one of</u> Ag and/or Al and other metal, a proportional content of said other metal being 0.001 - 10 percent by weight.

Claim 4 (Original): A semiconductor light-emitting element mounting member according to claim 3 wherein said other metal is at least one type of metal selected from a group consisting of Cu, Mg, Si, Mn, Ti, and Cr.

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Claim 5 (Canceled)

Claim 6 (Original): A semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed from Al alone or from an alloy of Al and other metal.

Claim 7 (Original): A semiconductor light-emitting element mounting member according to claim 1 wherein a thermal expansion coefficient of said substrate is 1×10^{-6} /K - 10×10^{-6} /K.

Claim 8 (Original): A semiconductor light-emitting element mounting member according to claim 1 wherein a thermal conductivity of said substrate is at least 80 W/mK.

Claim 9 (Original): A semiconductor light-emitting element mounting member according to claim 1 wherein said semiconductor light-emitting element mounting member is a flat submount.

Claim 10 (Original): A semiconductor light-emitting device wherein a semiconductor light-emitting element is mounted in a semiconductor light-emitting element mounting member according to claim 1.

Claim 11 (Original): A semiconductor light-emitting device according to claim 10 wherein output is at least 1 W.